

Subject card

Subject name and code	Solid state electronics, PG_00048718								
Field of study	Materials Engineering, Materials Engineering, Materials Engineering								
Date of commencement of studies	October 2021		Academic year of realisation of subject			2024/2025			
Education level	first-cycle studies		Subject group			Optional subject group Subject group related to scientific			
Made of study	Full time studies		Made of delivery			research in the field of study at the university			
Mode of study	Full-time studies		Mode of delivery			,			
Year of study	4		Language of instruction			Polish			
Semester of study	7		ECTS credits			3.0			
Learning profile	general academic profile			Assessment form			assessment		
Conducting unit	Zakład fizyki nanomateriałów -> Instytut Nanotechnologii i Inżynierii Materiałowej -> Faculty of Applied Physics and Mathematics								
Name and surname	Subject supervisor		prof. dr hab. inż. Barbara Kościelska						
of lecturer (lecturers)	Teachers		prof. dr hab. inż. Barbara Kościelska						
Lesson types and methods of instruction	Lesson type	Lecture	Tutorial	Laboratory	atory Project		Seminar	SUM	
	Number of study hours	30.0	0.0	0.0	0.0		15.0	45	
	E-learning hours included: 0.0								
Learning activity and number of study hours	Learning activity	Participation i classes including		Participation in consultation hours		Self-study		SUM	
	Number of study hours	45		5.0		25.0		75	
Subject objectives	The aim of the course is to gain knowledge, skills and competences of solid state electronics.								
Learning outcomes	Course outcome		Subject outcome			Method of verification			
	K6_W07		Detailed knowledge on selected issues of solid state electronics.			[SW1] Assessment of factual knowledge [SW2] Assessment of knowledge contained in presentation			
	K6_U06		Ability to analyze data and draw conclusions related to solid state electronics.			[SU2] Assessment of ability to analyse information			
	K6_W08		Knowledge of the development trend of solid state electronics.			[SW1] Assessment of factual knowledge			
	K6_K01		Ability to solve problems related to the implementation of specific tasks.			[SK5] Assessment of ability to solve problems that arise in practice			

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ct contents	1. Introduction.
	Physics and properties of solids - a review
	2.1. Density of states in 0D, 1D, 2D and 3D materials.
	2.2. Band structure of solids: free electron, nearly free electron and tight binding model.
	2.2. Energy hands and carrier apparatration in thermal equilibrium
	2.3. Energy bands and carrier concentration in thermal equilibrium.
	2.4. Electrical and thermal conduction in solids: carrier transport phenomena.
	2.5. Kinetic phenomena in semiconductors.
	Metal-semiconductor junctions and p-n junctions.
	4 Diodes: Schottky diode p-n diode MIS MOS tunneling diode resonant-tunneling diode
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	5. Transistors: bipolar, FET, hot-electron HET and THET, single-electron transistor.
	6. Light emitting diodes and lasers.
	6.1. Light emitting diodes.
	6.2. Semiconductor lasers.
	6.3. Quantum-cascade laser.
	7. Photodetectors and solar cells.
	9. Turnel phanemans in supersearch stars: Jacobbase junction
	o. Tunner prienomena in superconductors. Josephson junction.
	9. Spintronic devices.
	10. Semiconductor technology.
	10.1. Crystal growth and epitaxy.
	10.2 Film formation
	10.2. Film formation.
	10.3. Lithography and etching.
	10.4. Impurity doping.
	11. Summary.
uisites	Knowledge od mechanics, electricity and magnetism, basics of nanophysics, quantum mechanics.
-requisites	
uisites	 6. Light emitting diodes and lasers. 6.1. Light emitting diodes. 6.2. Semiconductor lasers. 6.3. Quantum-cascade laser. 7. Photodetectors and solar cells. 8. Tunnel phenomena in superconductors: Josephson junction. 9. Spintronic devices. 10. Semiconductor technology. 10.1. Crystal growth and epitaxy. 10.2. Film formation. 10.3. Lithography and etching. 10.4. Impurity doping. 11. Summary.

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Assessment methods and criteria	Subject passing criteria	Passing threshold	Percentage of the final grade				
	written exam	50.0%	66.0%				
	Seminar and presence on lessons	50.0%	34.0%				
Recommended reading	Basic literature 1. Aldert van der Ziel Podstawy fizyczne elektroniki ciała Stałego						
	2. C. Kittel Wstęp do fizyki ciała stałego						
	Supplementary literature 1. S.M. Sze Semiconductor Devices, Physics and Technology						
		24. O. Manasreh Semiconductor Heterojunctions and Na.					
	eResources addresses	Adresy na platformie eNauczanie:					
Example issues/ example questions/ tasks being completed	Crystalline structure of solids.						
	Models of electrons in crystals.						
	Semiconductors: band structure of semiconductors, carrier concentration; distribution functions.						
	Kkinetic phenomenas in semiconductors.						
	Contact phenomenas.						
	Diodes.						
	Transistors.						
	Lasers.						
	Tunneling processes in superconductors: Josephson junction.						
Work placement	Not applicable						

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